PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

Rev. 4 — 6 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	e number Package		NPN/PNP	PNP/PNP	Package	
	NXP	JEITA	complement	complement	configuration	
PEMH13	SOT666	-	PEMD13	PEMB13	ultra small and flat lead	
PUMH13	SOT363	SC-88	PUMD13	PUMB13	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMH13	-	plastic surface-mounted package; 6 leads	SOT666
PUMH13	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PEMH13	21
PUMH13	H0*

[1] * = placeholder for manufacturing site code

5. Limiting values

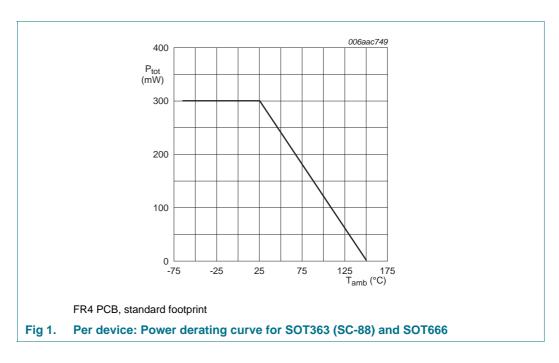
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
V_{I}	input voltage				
	positive		-	+30	V
	negative		-	-5	V
Io	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMH13 (SOT666)		[1][2] _	200	mW
	PUMH13 (SOT363)		<u>[1]</u> _	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMH13 (SOT666)		[1][2] _	300	mW
	PUMH13 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



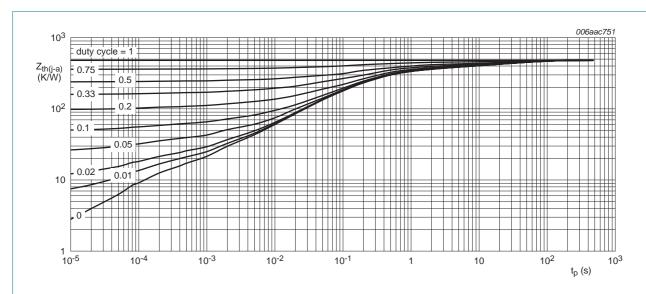
6. Thermal characteristics

Table 7. Thermal characteristics

· · (III(J-a)	resistance from to ambient	in free air				
· · (III(J-a)	to ambient	in free air				
	140 (OOTOO)					
PEMI	H13 (SOT666)		[1][2]	-	625	K/W
PUMI	H13 (SOT363)		<u>[1]</u> -	-	625	K/W
Per device						
· · · · · · · · · · · · · · · · · · ·	resistance from to ambient	in free air				
PEMI	H13 (SOT666)		[1][2] _	-	417	K/W
PUMI	H13 (SOT363)		<u>[1]</u> -	-	417	K/W

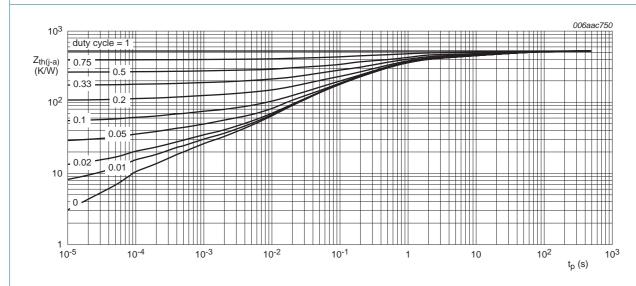
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH13 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH13 (SOT363); typical values

NPN/NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

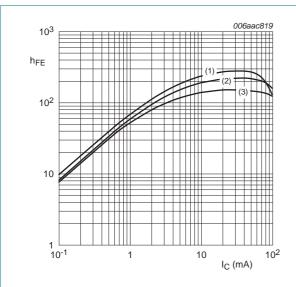
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$		-	-	1	μΑ
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	170	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$		-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$		1.3	0.9	-	V
R1	bias resistor 1 (input)		;	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			8	10	12	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	<u>[1]</u> .	-	230	-	MHz

^[1] Characteristics of built-in transistor

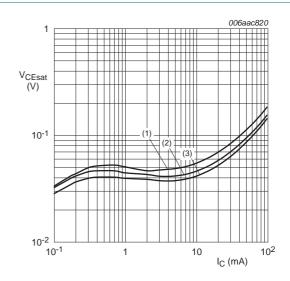


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



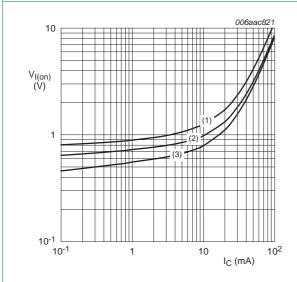
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



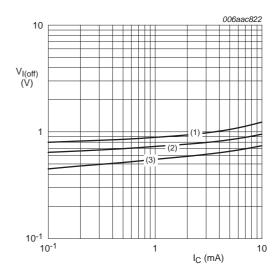
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



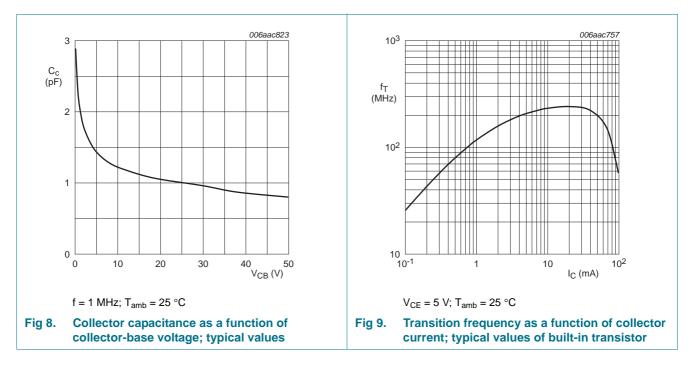
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

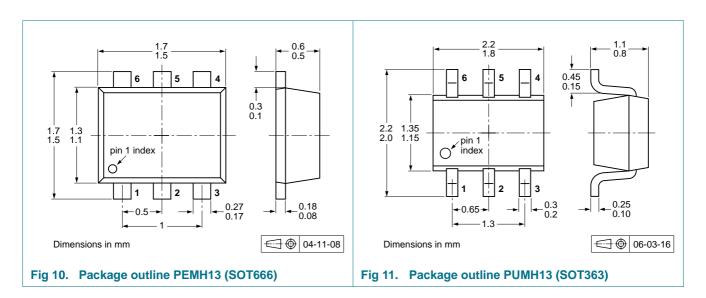


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH13 PUMH13

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10. Packing information

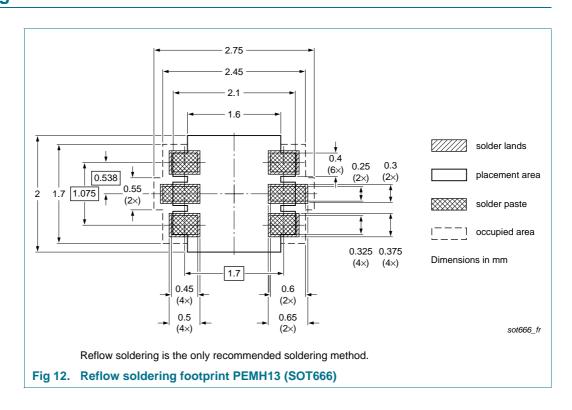
Table 9. Packing methods

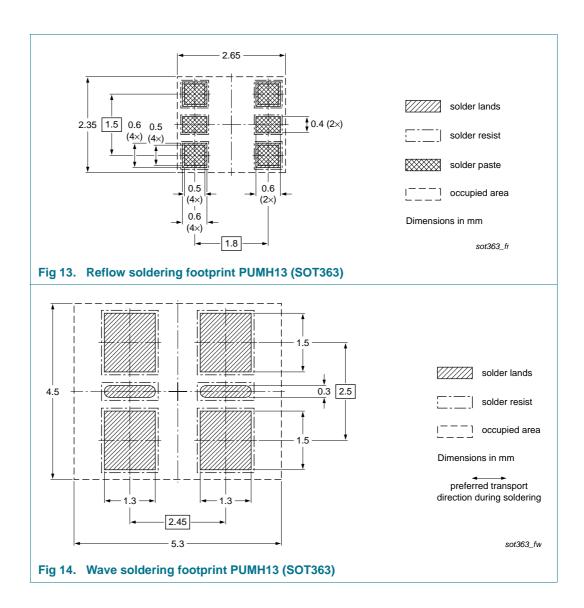
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description	Packin	g quant	ity	
number			3000	4000	8000	10000
PEMH13 SOT666		2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH13	SOT363	4 mm pitch, 8 mm tape and reel; T1 [2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





NPN/NPN resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMH13_PUMH13 v.4	20111206	Product data sheet	-	PEMH13_PUMH13 v.3		
Modifications:		of this document has been NXP Semiconductors.	redesigned to comply wi	th the new identity		
	 Legal texts h 	ave been adapted to the n	new company name whe	re appropriate.		
	 Section 1 "P 	roduct profile": updated				
	 Section 4 "M 	arking": updated				
	• <u>Figure 1</u> to 9	: added				
	 Section 5 "Li 	miting values": updated				
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 					
	Section 8 "Test information": added					
	Section 9 "Package outline": superseded by minimized package outline drawing					
	 Section 10 "I 	Packing information": adde	ed			
	 Section 11 "S 	Soldering": added				
	 Section 13 "I 	<u>_egal information"</u> : updated	d			
PEMH13_PUMH13 v.3	20040414	Product data sheet	-	PEMH13_PUMH13 v.2		
PEMH13_PUMH13 v.2	20031107	Product specification	-	PEMH13 v.1		
PEMH13 v.1	20011213	Preliminary specification	-	-		

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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PEMH13_PUMH13

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PEMH13; PUMH13

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

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